

Abstract

A thermal processing operation is performed for a silicon wafer W (silicon single-crystal layer) in an atmosphere gas which is formed by a hydrogen gas or an inert
5 gas or a mixture gas of these gases at a temperature in a range of 600 °C to 950 °C (here, the temperature should not be greater than 950 °C). By doing this, a quality of a surface of the silicon single-crystal layer is improved.